

**PUBLICATION LIST** Thorvald Andersson

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Black are inorganic materials – green are organic materials

*TEACHING***COURSE BOOKS**

Semiconductors and Heterostructures, Part 1 (230 pages), Textbook for the course “Semiconductor materials”, (2007).

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*PhD-THESIS*

Electrical and Structural Properties of Ultra Thin Metal Films, Department of Physics, Chalmers University of Technology and University of Göteborg, T Andersson, 1976.

*SCIENTIFIC PAPERS***UNDER PREPARATION**

The Effect on a QW Wave Function from an Inserted Barrier Layer, T.G. Andersson.

Growth of InGaN on sapphire by MBE, F Fälth and T G Andersson

Design of polarization-balanced quasi resonant-tunneling diodes in AlN/GaN heterostructures, Kristian Berland, Thorvald G. Andersson and Per Hyldgaard

**MANUSCRIPTS (under preparation)**

In- and Ga-adsorption on (0001) GaN surfaces studied by reflection high-energy electron diffraction, JF Fälth and T G Andersson

Annealing of c-plane sapphire for high-quality molecular beam epitaxy growth of III-nitrides, J.F. Fälth, S. K. Davidsson, X.Y. Liu, and T.G. Andersson

Superlattices and Multiple Quantum Wells in Nitride Heterostructures for QCLs Applications, Tommy Ive, Kristian Berland and Thorvald G. Andersson

**SUBMITTED****PUBLICATIONS (refereed)**

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10. Quantum Confined Stark Effect in Different Quantum Well Structures, (for the degree of Licentiate of Philosophy at the Department of Physics) W Chen, 1992.
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**OTHER PUBLICATIONS**

such as Journal publications or Conference participation and proceeding based on material grown in my group. I have no updated list but it contains more than 50 papers/contributions.